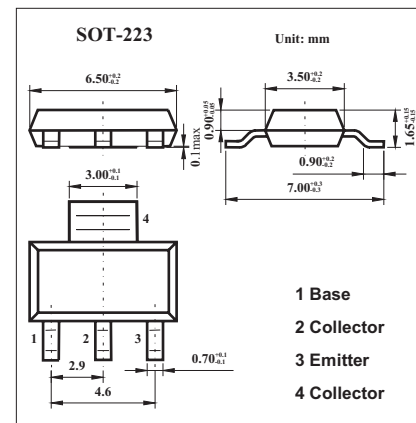


PNP High-Voltage Transistor

BSP16

■ Features

- High voltage (max. 350 V).

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
collector-base voltage (open emitter)	V_{CB0}	-350	V
collector-emitter voltage (open base)	V_{CE0}	-300	V
emitter-base voltage (open collector)	V_{EB0}	-6	V
collector current (DC)	I_C	-200	mA
base current (DC)	I_B	-200	mA
total power dissipation $T_{amb} \leq 25^\circ\text{C}^*$	P_{tot}	1.28	W
storage temperature	T_{stg}	-65 to 150	$^\circ\text{C}$
junction temperature	T_j	150	$^\circ\text{C}$
operating ambient temperature	T_{amb}	-65 to 150	$^\circ\text{C}$
thermal resistance from junction to ambient *	$R_{th\ j-a}$	97	K/W
thermal resistance from junction to soldering point	$R_{th\ j-s}$	16	K/W

*. Device mounted on printed-circuit board, single sided copper, tinplated, mounting pad for collector 1 cm^2 .

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
collector cut-off current	I_{CBO}	$I_E = 0; V_{CB} = -280\text{ V}$			-100	nA
emitter cut-off current	I_{EBO}	$I_C = 0; V_{EB} = -6\text{ V}$			-100	nA
DC current gain	h_{FE}	$I_C = -50\text{ mA}; V_{CE} = -10\text{ V}$	30		120	
collector-emitter saturation voltage	V_{CEsat}	$I_C = -50\text{ mA}; I_B = -5\text{ mA}$			-2	V
collector capacitance	C_c	$I_E = I_C = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$			15	pF
transition frequency	f_T	$I_C = -10\text{ mA}; V_{CE} = -10\text{ V}; f = 100\text{ MHz}$	15			MHz